

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SC2620

Silicon NPN Epitaxial Planar

RENESAS

ADE-208-1071 (Z)

1st. Edition

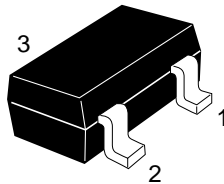
Mar. 2001

Application

VHF amplifier, Local oscillator

Outline

MPAK



- 1. Emitter
- 2. Base
- 3. Collector

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	4	V
Collector current	I_C	20	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

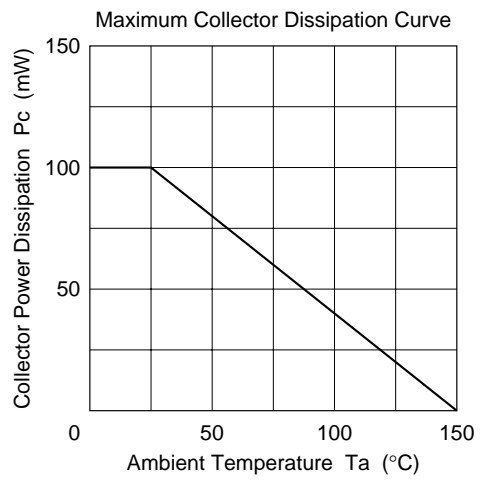
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	V	$I_C = 10\text{ }\mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	—	—	V	$I_C = 1\text{ mA}$, $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	4	—	—	V	$I_E = 10\text{ }\mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 10\text{ V}$, $I_C = 0$
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	$V_{EB} = 2\text{ V}$, $I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	60	—	200		$V_{CE} = 6\text{ V}$, $I_C = 1\text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.17	—	V	$I_C = 20\text{ mA}$, $I_B = 4\text{ mA}$
Base to emitter voltage	V_{BE}	—	0.72	—	V	$V_{CE} = 6\text{ mA}$, $I_C = 1\text{ mA}$
Gain bandwidth product	f_T	—	940	—	MHz	$V_{CE} = 6\text{ V}$, $I_C = 5\text{ mA}$
Collector output capacitance	C_{ob}	—	0.9	—	pF	$V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$

Note: 1. The 2SC2620 is grouped by h_{FE} as follows.

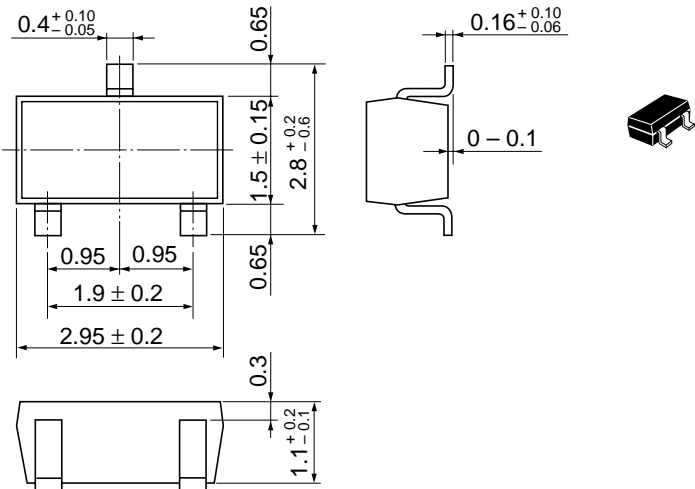
Grade	B	C
Mark	QB	QC
h_{FE}	60 to 120	100 to 200

See characteristic curves of 2SC535.



Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.011 g

Cautions

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